

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S2	7440	(AFM STEM SEM nanotip\$3 probe atomic adj force scanning near microscope) and ((si silicon) near (n p dop\$4) n-type p-type) and etch\$3	US-PGPU B; USPAT	OR	ON	2005/09/28 11:22
S3	1023	S2 and (((si silicon) near (n dop\$4) n-type) with etch\$3) and (((si silicon) near (p dop\$4) p-type) with etch\$3)	US-PGPU B; USPAT	OR	ON	2005/09/28 11:25
S4	960	S2 and (((si silicon) near (n dop\$4) n-type) with etch\$3) same (((si silicon) near (p dop\$4) p-type) with etch\$3)	US-PGPU B; USPAT	OR	ON	2005/09/28 11:25
S5	943	S2 and (((si silicon) near (n dop\$4) n-type) with etch\$3) with (((si silicon) near (p dop\$4) p-type) with etch\$3)	US-PGPU B; USPAT	OR	ON	2005/09/28 11:25
S6	358	S2 and (((si silicon) near n n-type) with etch\$3) with (((si silicon) near p p-type) with etch\$3)	US-PGPU B; USPAT	OR	ON	2005/09/28 11:26
S7	4	S2 and (((si silicon) near n n-type) near etch\$3) with (((si silicon) near p p-type) near etch\$3)	US-PGPU B; USPAT	OR	ON	2005/09/28 11:27
S8	17	S2 and (((si silicon) near n n-type) near2 etch\$3) with (((si silicon) near p p-type) near2 etch\$3)	US-PGPU B; USPAT	OR	ON	2005/09/28 11:27
S9	40	S2 and (((si silicon) near n n-type) near4 etch\$3) with (((si silicon) near p p-type) near4 etch\$3)	US-PGPU B; USPAT	OR	ON	2005/09/28 11:27

S10	46	("3977925"   "4312117"   "4668865"   "4806755"   "4943719").PN. OR ("5021364").URPN.	US-PGPU B; USPAT; USOCR	OR	OFF	2005/09/28 11:38
S11	13	S8 not S7	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/09/28 11:43
S12	23	S9 not (S7 S8)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/09/28 11:43
S13	5	(cant?lever AFM STEM SEM nanotip\$3 probe atomic scanning microscope) near2 tip with ((si silicon) near (n p dop\$4) n-type p-type) with etch\$3	US-PGPU B; USPAT	OR	ON	2005/09/28 11:50
S14	70	("3977925"   "4307507"   "4312117"   "4668865"   "4685996"   "4806755"   "4912822"   "4916002"   "4943719"   "4968382"   "4968585").PN. OR ("4943719"   "5066358").URPN.	US-PGPU B; USPAT; USOCR	OR	OFF	2005/09/28 11:52
S16	92	S10 S14	US-PGPU B; USPAT; USOCR	OR	OFF	2005/09/28 11:52
S15	24	S10 and S14	US-PGPU B; USPAT; USOCR	OR	OFF	2005/09/28 11:59

S17	68	S16 not S15	US-PGPU B; USPAT; USOCR	OR	OFF	2005/09/28 11:59
S18	28	(US-5021364-\$ or US-5066358-\$ or US-4943719-\$ or US-6011261-\$ or US-5811017-\$ or US-5717132-\$ or US-5469733-\$ or US-5386720-\$ or US-5386110-\$ or US-5367165-\$ or US-5264696-\$ or US-6886395-\$ or US-6862921-\$ or US-6694805-\$ or US-6400166-\$ or US-6358426-\$ or US-6059982-\$ or US-5994160-\$ or US-5929643-\$ or US-5595942-\$ or US-5580827-\$ or US-5537863-\$ or US-5272913-\$ or US-5116462-\$ or US-4968585-\$ or US-4916002-\$).did. or (US-4685996-\$ or US-4307507-\$).did.	USPAT	OR	OFF	2005/09/28 12:26

S19	18	(US-6694805-\$ or US-6059982-\$ or US-6011261-\$ or US-5994160-\$ or US-5929643-\$ or US-5717132-\$ or US-5580827-\$ or US-5537863-\$ or US-5469733-\$ or US-5367165-\$ or US-5272913-\$ or US-5116462-\$ or US-5021364-\$ or US-4968585-\$ or US-4943719-\$ or US-4916002-\$ or US-4685996-\$ or US-4307507-\$).did.	USPAT	OR	OFF	2005/09/28 12:32
S21	0	S20 and ((square rectang\$4 pyramid\$4) near (mask\$3 photoresist opening pit hole expos\$4)) and (deposit\$4 near (first second) near (dop\$3 si silicon)) and (etch\$3 near (Si silicon))	US-PGPU B; USPAT	OR	ON	2005/09/28 12:41
S22	0	S20 and ((square rectang\$4 pyramid\$4) near2 (mask\$3 photoresist opening pit hole expos\$4)) and (deposit\$4 near2 (first second) near2 (dop\$3 si silicon)) and (etch\$3 near2 (Si silicon))	US-PGPU B; USPAT	OR	ON	2005/09/28 12:41
S23	8	S20 and ((square rectang\$4 pyramid\$4) with (mask\$3 photoresist opening pit hole expos\$4)) and (deposit\$4 with (first second) near2 (dop\$3 si silicon)) and (etch\$3 with (Si silicon))	US-PGPU B; USPAT	OR	ON	2005/09/28 12:43

S24	32	S20 and ((square rectang\$4 pyramid\$4) with (mask\$3 photoresist opening pit hole expos\$4)) and (deposit\$4 with (first second) with (dop\$3 si silicon)) and (etch\$3 with (Si silicon))	US-PGPU B; USPAT	OR	ON	2005/09/28 12:44
S26	4	S25 and S24	US-PGPU B; USPAT	OR	ON	2005/09/28 12:44
S27	3	S23 and S25	US-PGPU B; USPAT	OR	ON	2005/09/28 12:44
S28	4	S26 S27	US-PGPU B; USPAT	OR	ON	2005/09/28 12:57
S1	5998	(AFM STEM SEM nanotip\$3 probe atomic adj force scanning near microscope) and (si near (n p dop\$4) n-type p-type) and etch\$3	US-PGPU B; USPAT	OR	ON	2005/09/28 12:58
S30	4	S29 and (n p dop\$4 n-type p-type)	US-PGPU B; USPAT	OR	ON	2005/09/28 13:11
S32	1	S31 not S30	US-PGPU B; USPAT	OR	ON	2005/09/28 13:11
S29	5	S23 not S28	US-PGPU B; USPAT	OR	ON	2005/09/28 13:13
S33	0	S29 not S23	US-PGPU B; USPAT	OR	ON	2005/09/28 13:13





S34	24	S24 not S23	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/09/28 13:15
S36	0	S35 not S34	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/09/28 13:16
S37	2	S34 not S35	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/09/28 13:16
S35	22	S34 and (p n p-type n-type dop\$4)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/09/28 13:36
S31	5	S29 and (n p dop\$4 n-type p-type etch\$3)	US-PGPU B; USPAT	OR	ON	2005/09/28 14:03
S40	59	S39 and (n p dop\$4 n-type p-type)	US-PGPU B; USPAT	OR	ON	2005/09/28 14:03
S41	207	(n-type p-type dop\$3) near (Si silicon) with (\$6probe \$6tip stylus)	US-PGPU B; USPAT	OR	ON	2005/09/28 14:55
S25	38	S20 and electrochemical\$2 with etch\$3	US-PGPU B; USPAT	OR	ON	2005/09/28 14:57

S42	23	S41 and electrochemical\$2 with etch\$3	US-PGPU B; USPAT	OR	ON	2005/09/28 14:57
S38	22	S34 and (p n p-type n-type dop\$4)	US-PGPU B; USPAT	OR	ON	2005/09/28 15:07
S43	23	S42 and (p n p-type n-type dop\$4)	US-PGPU B; USPAT	OR	ON	2005/09/28 15:07
S39	83	("3977925"   "4008412"   "4307507"   "4312117"   "4668865"   "4724318"   "4806755"   "5057047"   "5214282"   "5272330"   "5354985"   "5357787"   "5410151"   "5489774"   "5580827"   "5811926"). PN. OR ("4943719"   "5883387"   "5962958"). URPN.	US-PGPU B; USPAT; USOCR	OR	OFF	2005/09/28 15:21
S45	17	(n-type p-type dop\$3) near (Si silicon) near (\$2AFM \$6probe \$6tip stylus)	US-PGPU B; USPAT	OR	ON	2005/10/03 15:36
S46	1	deposit\$4 near (n-type p-type dop\$3) near (Si silicon) near (\$2AFM \$6probe \$6tip stylus)	US-PGPU B; USPAT	OR	ON	2005/10/03 15:38
S48	1	deposit\$4 near4 (n-type p-type dop\$3) near4 (Si silicon) near4 (\$2AFM \$6probe \$6tip stylus)	EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/03 15:43
S49	56	deposit\$4 same (n-type p-type dop\$3) same (Si silicon) same (\$2AFM \$6probe \$6tip stylus)	EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/03 15:43
S47	11	deposit\$4 near4 (n-type p-type dop\$3) near4 (Si silicon) near4 (\$2AFM \$6probe \$6tip stylus)	US-PGPU B; USPAT	OR	ON	2005/10/03 16:00



S50	42	deposit\$4 with (n-type p-type dop\$3) with (Si silicon) with (\$2AFM \$6probe \$6tip stylus)	US-PGPU B; USPAT	OR	ON	2005/10/03 16:01
S51	31	S50 not S47	US-PGPU B; USPAT	OR	ON	2005/10/03 16:01
S53	123	dop\$3 near (Si silicon) with (\$2AFM \$6probe \$6tip stylus)	US-PGPU B; USPAT	OR	ON	2005/10/03 16:32
S44	218	(n-type p-type dop\$3) near (Si silicon) with (\$2AFM \$6probe \$6tip stylus)	US-PGPU B; USPAT	OR	ON	2005/10/03 16:33
S55	74	S54 and electrochemical\$2 near4 etch\$3	US-PGPU B; USPAT	OR	ON	2005/10/03 16:34
S56	48	S55 not S52	US-PGPU B; USPAT	OR	ON	2005/10/03 16:34
S52	26	S44 and electrochemical\$2 near4 etch\$3	US-PGPU B; USPAT	OR	ON	2005/10/03 16:39
S54	1336	(n-type p-type dop\$3) with (Si silicon) same (\$2AFM \$6probe \$6tip stylus)	US-PGPU B; USPAT	OR	ON	2005/10/03 16:39
S57	194	(n-type p-type dop\$3) with (Si silicon) same (\$2AFM \$6probe \$6tip stylus)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:39
S58	0	S57 and electrochemical\$2 near4 etch\$3	US-PGPU B; USPAT	OR	ON	2005/10/03 16:39
S59	5	S57 and electrochemical\$2 near4 etch\$3	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:39